## ECE 320 - Homework \#9

TTL Logic, MOSFET Theory, MOSFET Switches. Due Monday, March 19th

## TTL Logic:

1) Determine the voltages and currents for the following TTL AND gate. Assume ideal silicon diodes and transistors with $\beta=100$.


## MOSFET:

2a) Label the Off / Saturated / Ohmic regions for the following n-channel MOSFET
2b) Determine the transconductange gain, $\mathrm{kn}\left(\mathrm{V}_{\mathrm{th}}=1.0 \mathrm{~V}\right)$


3a) Draw the load line for the following circuit on the previous graph
3b) Determine the Q-point (Vds, Ids) when

- $\mathrm{Vg}=0 \mathrm{~V}$
- $\mathrm{Vg}=3 \mathrm{~V}$
- $\mathrm{Vg}=6 \mathrm{~V}$

Assume a AOT2618L n-channel MOSFET:

- 23A max continuous current Ids
- 70A max pulse current
- 19 mOhm @ 20A @ Vgs = 10V
- Vth $=2.5 \mathrm{~V}$ (max)
- $\$ 0.72$ (qty = 100)
- Digikey part number: 785-1438-5-ND

4) Determine the transconductance gain, kn
5) Determine the voltages for the MOSFET circuit to the right
6) Modify this circuit so that Ids $=1 \mathrm{~A}$ when Vin $=5 \mathrm{~V}$.

